What is claimed:

Sub A'

1. A driver circuit comprising a semiconductor integrated circuit having a transistor in which a drive signal is applied to the transistor to drive the transistor to thereby drive a load, the driver circuit comprising:

a signal line that supplies the drive signal, the signal line being separated from the transistor by a dielectric layer; and

at least two connection sections that connect the signal line to a gate electrode of the transistor, the connection sections being provided in a width direction of the gate electrode.

2. A driver circuit comprising a semiconductor integrated circuit having a plurality of transistors in which a single drive signal is applied to each of the transistors to drive the transistors to thereby drive a load, the driver circuit comprising:

a signal line that supplies the drive signal, the signal line being separated from each of the transistors by a dielectric layer; and

at least two connection sections that connect the signal line to a gate electrode of at least one of the transistors, the connection sections being provided in a width direction of the gate electrode.

3. A driver circuit according to claim 2, wherein the at least two connection sections includes two or more connection sections provided for each of the transistors.

4. A driver circuit according to claim 2, wherein the at least two connection sections includes two or more connection sections provided for each of the transistors except one of the transistors.

5. A driver circuit according to claim 2, wherein at least two of the plurality of transistors have a different number of connection sections.

6. A driver circuit according to claim 3, wherein at least two of the plurality of transistors have a different number of connection sections.

7. A driver circuit according to claim 4, wherein at least two of the plurality of transistors have a different number of connection sections.

8. A driver circuit according to claim 2, wherein the plurality of transistors have different numbers of connection sections.

9. A driver circuit comprising a semiconductor integrated circuit having a plurality of transistors in which a single drive signal is applied to each of the transistors to drive the transistors to thereby drive a load, the driver circuit comprising:

a signal line that supplies the drive signal, the signal line being separated from each of the transistors by a dielectric layer; and

connection sections for connecting the signal line to a gate electrode of each of the transistors, the connection sections being provided in a width direction of the gate electrode, wherein at least two of the plurality of transistors have a different number of connection sections.

10. A driver circuit according to claim 9, wherein the plurality of transistors have different numbers of connection sections.

11. A method for manufacturing a driver circuit including a semiconductor integrated circuit having a plurality of transistors in which a single drive signal is applied to each of the transistors to drive the transistors to thereby drive a load, the method comprising:

forming a gate electrode for each of the transistors on a substrate that includes a semiconductor region;

forming a dielectric layer over the transistors;

forming contact holes in the dielectric layer for connecting signal lines that supply the drive signal to the gate electrodes, the signal lines being located in a layer above the dielectric layer; and

forming the signal lines over the dielectric layer,

wherein two or more of the contact holes are formed for at least one of the plurality of transistors in the contact hole forming step.